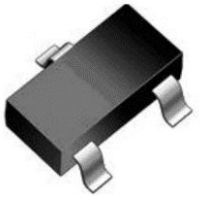
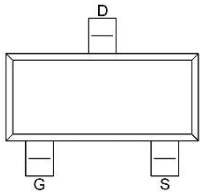
-30V_{DS}/±20V_{GS} P-Channel Enhancement Mode MOSFET

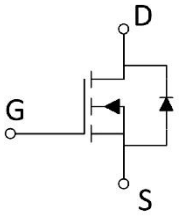
Features

- V_{DS}=-30V,I_D=-4.2A
- $R_{DS(ON)}$=60mΩ（TYP.）V_{GS}=10V
- $R_{DS(ON)}$=87mΩ（TYP.）V_{GS}=4.5V

SOT23-3L







Applications

- Portable device
- Switch switching

Ordering Information

Device	package	Device Marking	Package Qty.
JMTJ3407A	SOT-23-3L	R7/X7	3000/PCS
JMTJ3407A	SOT-23	R7/A7	3000/PCS

Absolute Maximum Ratings (T$_C$=25℃,unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V)	V_{DS}	-30	V
Gate-Source Voltage (V_{GS}=0V,static)	V_{GS}	±20	V
Continuous Drain Current (T_C=25℃)	I_D	-4.1	A
Pulesd Drain Current	I_{DM}	20	A
Maximum Power Dissipation (T_C=25℃)	P_D	1.25	W
Operating,Storage Temperature Range	T_J,T_{STG}	-55~150	℃

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	-	60	-	℃/ W
Thermal Resistance,Junction-to-Ambient	$R_{\theta JA}$	-	100	-	℃/ W

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V, V_{GS}=0V	-	-	1	μA
Gate -Source Leakage Current	I_{GSS}	V_{GS}=±12V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS},I_D=250μA	1	1.4	3	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=5.8A	-	46	65	mΩ
		V_{GS}=4.5V,I_D=5A	-	68	90	

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	V_{DS}=15V	-	700	-	pF
Output capacitance	C_{oss}	V_{GS}=0V	-	120	-	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	75	-	
Gate Resistance	R_g	f=1MHz	-	1.4	-	Ω
Total Gate Charge	Q_g	V_{DS}=15V	-	7.2	-	nC
Gate Source Charge	Q_{gs}	V_{GS}=4.5V	-	1.5	-	
Gate Drain Charge	Q_{gd}	I_D=5.8A	-	2.6	-	
Turn-on delay Time	$t_{d(on)}$	V_{GS}=10V	-	8.6	-	ns
Rise time	t_r	V_{DS}=15V	-	5.0	-	
Turn-off delay Time	$t_{d(off)}$	R_L=2.7Ω	-	28.2	-	
Fall time	t_f	R_G=3Ω	-	13.5	-	

Reverse Diode Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Body Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_{SD}=1A	-	-	1.0	V
Reverse Recovery Time	t_{rr}	V_{GS}=0V,I_{SD}=5A	-	16	-	ns
Reverse Recovery Charge	Q_{rr}	d_i/d_t=100A/μs	-	9	-	nC